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FIG. 1

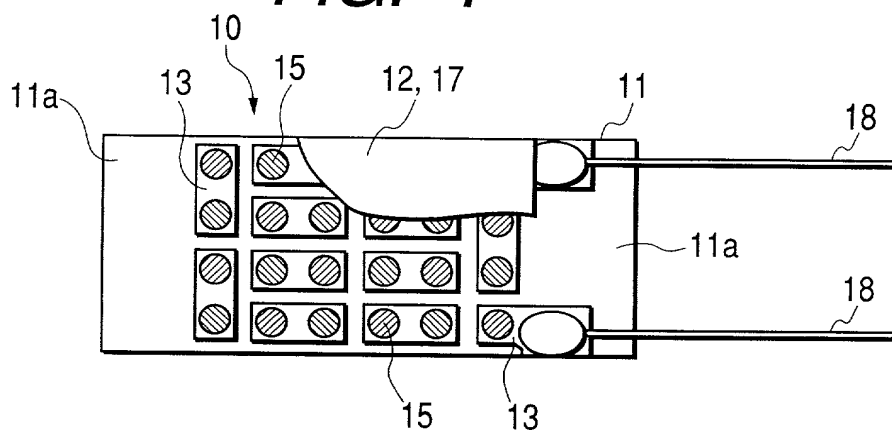


FIG. 2

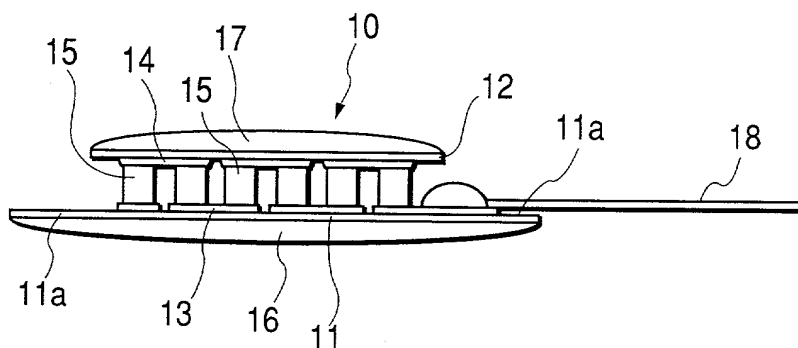
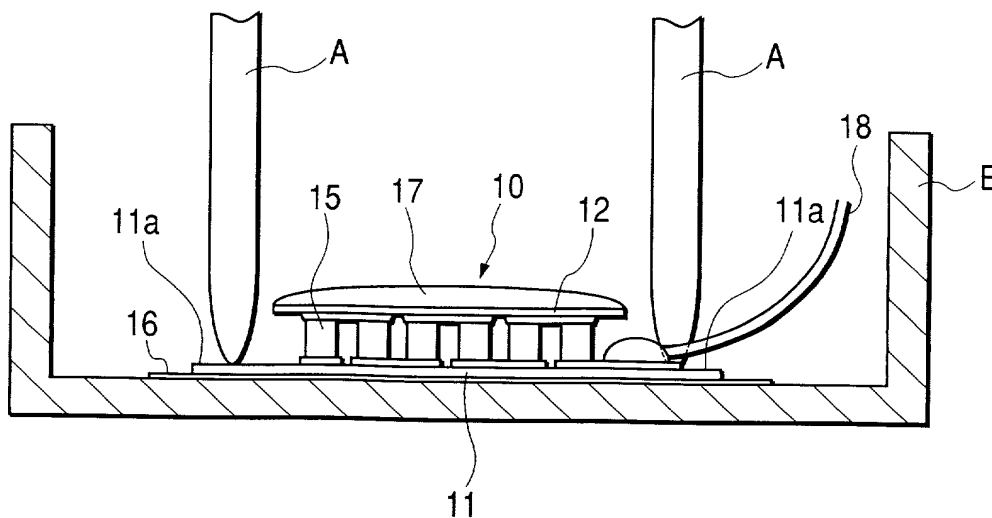


FIG. 3



A cross-sectional view of a semiconductor device 10. The device features a substrate 11 with a top surface 11a and a bottom surface 11b. A layer 12 is formed on the top surface 11a. A series of vertical structures 13 are formed on the top surface 11a, each consisting of a central core 14 and a surrounding layer 15. A layer 16 is formed on the top surface 11a, covering the vertical structures 13. A layer 17 is formed on the top surface 11a, covering the layer 16. A layer 18 is formed on the bottom surface 11b, extending laterally from the device.

A cross-sectional view of a semiconductor device assembly. The assembly is mounted on a substrate 11. A central component 10 is shown, which includes a base layer 12, a series of vertical pillars 15, and a top layer 17. This central component is flanked by two side components 11b. The side components 11b are connected to the substrate 11 at points 11a. A layer 16 is located between the side components 11b and the central component 10. A layer 18 is shown on the right side component 11b. The entire assembly is enclosed within a frame 11.

FIG. 7

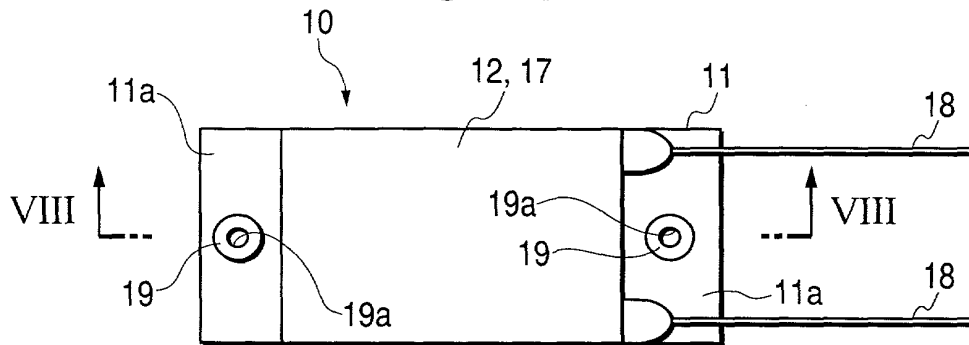


FIG. 8

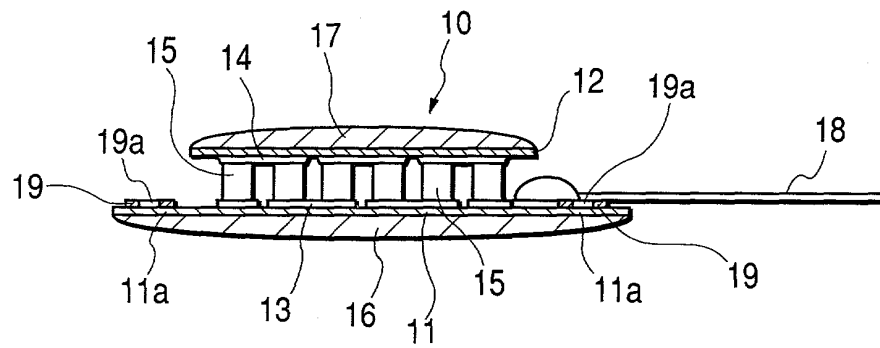
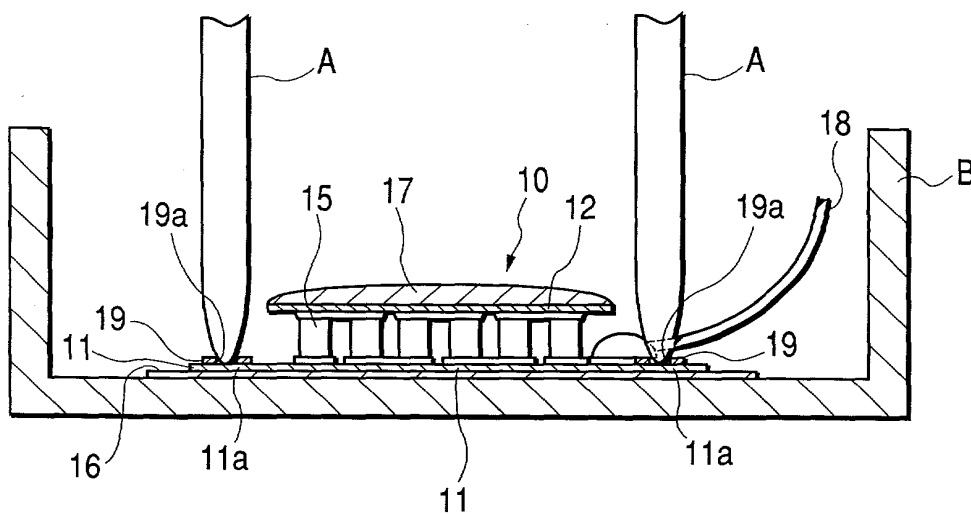


FIG. 9



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FIG. 10
RELATED ART

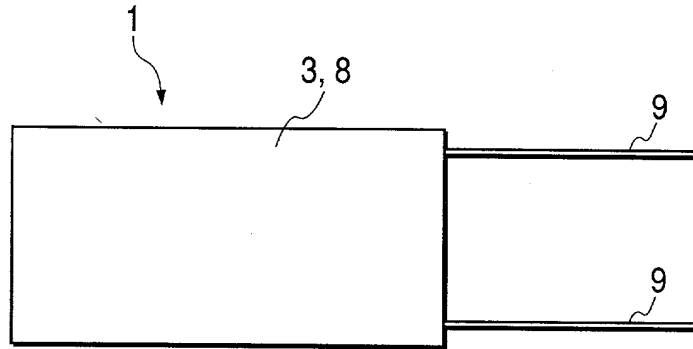


FIG. 11
RELATED ART

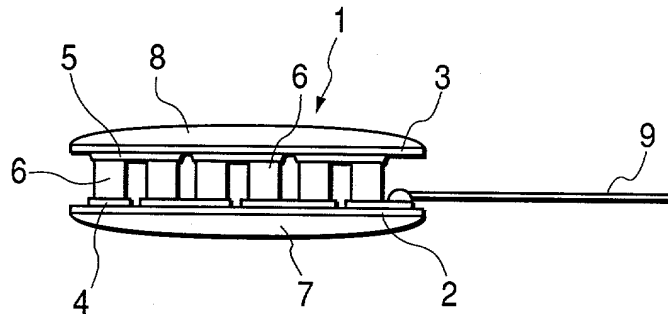
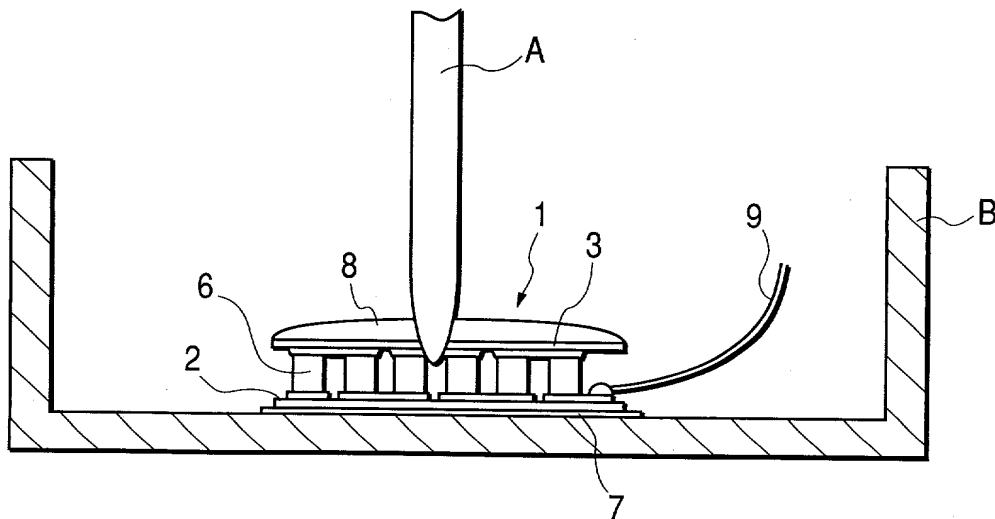


FIG. 12
RELATED ART



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FIG. 13

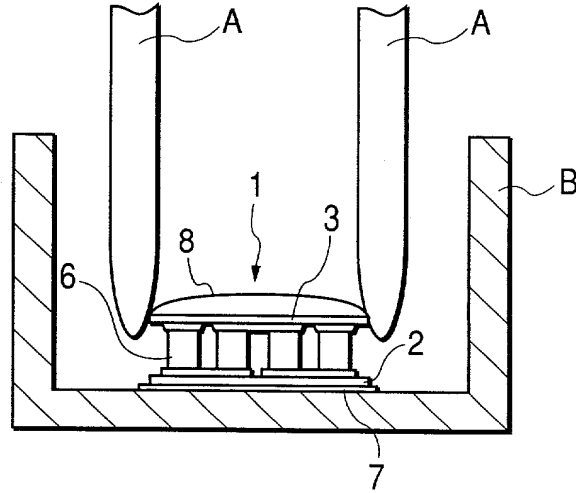


FIG. 14

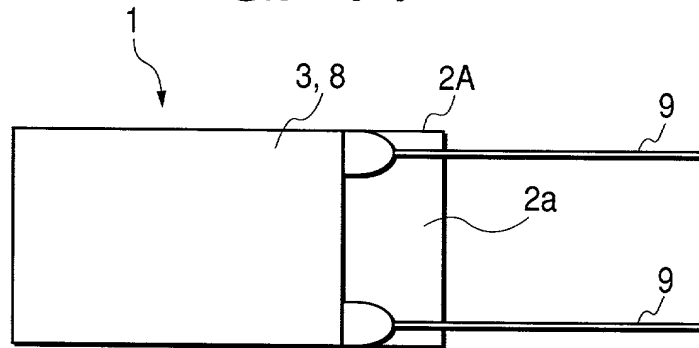


FIG. 15

